STANDARD OPERATING PROCEDURE: THIN-FILM METROLOGY & CHARACTERIZATION

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Author / Lead Tech: Kadeem Manning (Tier II)	**Department:** Thin-Film & Dielectric Metrology Lab	**Status: APPROVED & ACTIVE**
Field Ops Manager: Mark Tigges	**QA Manager:** Genevieve Lariviere	**Compliance:** ALCOA+ / NIST Traceable

1. PURPOSE, SCOPE & CLEANROOM SAFETY PROTOCOLS

This Standard Operating Procedure (SOP) defines the standardized multi-instrument metrology workflows for characterizing deposited dielectric, semiconductor, and metallic thin films on silicon, quartz, alumina, and flexible composite substrates. All characterization procedures guarantee ALCOA+ data integrity and NIST traceability across non-contact optical, mechanical stylus profilometry, four-point probe sheet resistance, and high-frequency microwave dielectric S-parameter extraction.
Cleanroom & EHS Mandates: All measurements must be performed in an ISO Class 6 cleanroom environment. Technicians must wear 6 mil powder-free nitrile gloves and ANSI Z87.1 safety eyewear. Substrates must be handled exclusively using non-marking Teflon or vacuum tweezers along perimeter edges (≤1.0 mm contact). Laser-based instruments (ellipsometers, optical profilometers) operate under Class 3B/4 safety controls per ANSI Z136.1; beam paths must remain shielded during alignment sweeps.

2. METROLOGY INSTRUMENT SUITE & SPECIFICATIONS MATRIX

Instrument Technique	Primary Parameters	Operating Range / Accuracy	Calibration Standard & Freq
Spectroscopic Ellipsometry	Thickness (d), Refractive Index (n), Extinction (k)	0.5 nm – 5.0 µm; Accuracy ±0.2 nm (Cauchy / Tauc-Lorentz)	NIST 100 nm SiO_2/Si wafer; Daily zero alignment
Stylus Profilometry	Step height, surface roughness (R_a, R_q)	10 nm – 100 µm step height; 2.5 µm diamond tip @ 15 mg force	VLSI 1.0 µm step height standard; Weekly check
Quartz Crystal Microbalance	In-situ deposition rate (Å/s) and acoustic mass thickness	0.1 Å/s – 50 Å/s; Sauerbrey mass resolution <1.0 ng/cm^2	6 MHz AT-cut quartz crystal; Pre-run Z-factor check
Four-Point Probe	Sheet resistance (R_s), electrical conductivity (σ)	10 mΩ/sq – 100 kΩ/sq; Dual-configuration current sweep	NIST-traceable FPP calibration wafer; Monthly audit
VNA Microwave Resonator	Complex permittivity (ε_r', ε_r''), loss tangent (tan δ)	1.0 GHz – 20.0 GHz; S_{11}/S_{21} resonance shift & Q-factor	Electronic Calibration Module (eCal SOLT); Daily 2-port

3. STEP-BY-STEP CHARACTERIZATION PROCEDURES

Phase 1: Optical Ellipsometry & Index Fitting (200 nm – 1000 nm):
1. Turn on xenon arc lamp and allow a 15-minute thermal stabilization period.
2. Load NIST-traceable 100 nm SiO_2/Si reference wafer onto vacuum chuck. Execute intensity auto-alignment at $\phi = 70°$.
3. Measure ellipsometric angles Psi (Ψ) and Delta (Δ) across 300–800 nm. Verify fit error MSE < 2.5 against NIST certified thickness.
4. Load target thin-film sample. Acquire Ψ/Δ spectrum at 65°, 70°, and 75° incident angles.
5. Apply transparent Cauchy model for dielectrics (SiO_2, Al_2O_3) or Tauc-Lorentz oscillator model for absorbing/semiconducting films. Extract thickness d (nm), n(632.8 nm), and extinction coefficient k.

Phase 2: Stylus Profilometry Step-Height Verification:
1. Ensure sample features a sharp shadow-masked or etched step-edge.
2. Set scan length = 1.0 mm, scan speed = 50 µm/s, and stylus force = 15 mg (147 µN) to prevent film scratching.
3. Perform 3 parallel profile scans across the step edge. Apply leveling baselines to raw data on both sides of the step.
4. Calculate average step height d_{prof} and surface roughness R_a. Confirm step height agrees with ellipsometry within ±3%.

Phase 3: Four-Point Probe Sheet Resistance & Conductivity:
1. Check probe head alignment; verify carbide/gold needle spacing s = 1.0 mm and probe tip radius = 100 µm.
2. Lower probe head onto metallic or TCO thin film; confirm contact force = 100 grams.

3. Apply forward and reverse DC currents (1.0 mA to 10.0 mA) to cancel thermoelectric EMF offsets.
4. Record forward/reverse voltage drops. Calculate sheet resistance $R_s = (\pi / \ln 2) \cdot (V / I) \cdot F(t/s)$. Compute electrical conductivity $\sigma = 1 / (R_s \cdot d)$.

Phase 4: Microwave S-Parameter Dielectric Permittivity Extraction (1–20 GHz):
1. Perform full 2-port SOLT calibration on Vector Network Analyzer (VNA) using Electronic Calibration Module.
2. Connect microstrip / SIW planar resonator sensor fixture or open-ended coaxial dielectric probe.
3. Measure baseline resonance frequency f_0 and quality factor Q_0 for empty fixture.
4. Mount thin-film dielectric sample flush against sensing plane without air gaps (<5 µm tolerance).
5. Record shifted resonance frequency f_r and loaded Q_L. Calculate real permittivity ε_r' from frequency shift and loss tangent $\tan \delta = \varepsilon_r'' / \varepsilon_r'$ from $1/Q$ bandwidth broadening.

4. DATA DEFENSIBILITY, CALIBRATION CONTROLS & SIGN-OFF

ALCOA+ Data Integrity & CMMS Archiving: All raw spectrum files (.dat, .s2p, .csv) and fitted model reports must be saved contemporaneously to the network server. Upload 300 DPI PDF characterization certificates to CMMS Work Orders within 24 hours. Any out-of-spec measurement (>5% thickness discrepancy or fit MSE > 5.0) triggers an immediate Level 1 QA hold on the substrate batch.

Prepared By: Kadeem Manning Tier II Vacuum Lab Specialist	**Reviewed By:** Mark Tigges Field Operations Manager	**Approved By:** Genevieve Lariviere QA Program Manager
Signature: *Kadeem Manning*	**Signature:** *Mark Tigges*	**Signature:** *Genevieve Lariviere*
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